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Fairchild Semiconductor 2N6519BU

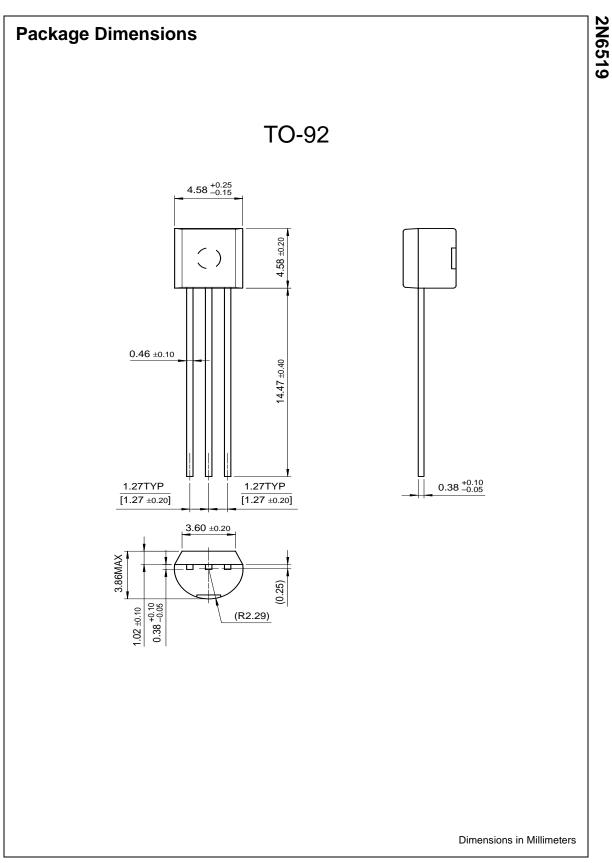
For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



	2	N6519				
Collector- Collector	Ditage Transistor Emitter Voltage: V _{CEO} = -300V Dissipation: P _C (max)=625mW pitaxial Silicon Transist	1 :Or 1. Er	Tunitter 2. Base	O-92 e 3. Colle	ector	
bsolut	te Maximum Ratings T _{a=25°} C u	Inless otherwise noted				
Symbo		er	Value	ι	Units	
V _{CBO}	Collector-Base Voltage		-300		V	
V _{CEO}	Collector-Emitter Voltage		-300		V	
V _{EBO}	Emitter-Base Voltage		-5		V	
С	Collector Current		-500		mA	
В	Base Current		-250		mA	
Pc	Collector Power Dissipation		625		W	
	Derate above 25°C		5	m	W/°C	
Г _Ј	Junction Temperature		150 °C		-	
T _{STG} Refer to 2N652	Storage Temperature		-55 ~ 150		°C	
	al Characteristics T _a =25°C unles	53 Uniel Wise Holeu				
Symbol	Parameter	Test Condition	Min.	Max.		
BV _{CBO}	Parameter Collector-Base Breakdown Voltage	I _C = -100μA, I _E =0	-300	Max.	V	
BV _{CBO} BV _{CEO}	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage	I_{C} = -100µA, I_{E} =0 I_{C} = -1mA, I_{B} =0	-300 -300	Max.	V V	
BV _{CBO} BV _{CEO} BV _{EBO}	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage	I_{C} = -100µA, I_{E} =0 I_{C} = -1mA, I_{B} =0 I_{E} = -10µA, I_{C} =0	-300		V V V	
BV _{CBO} BV _{CEO} BV _{EBO}	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current	$I_{C}=-100\mu A, I_{E}=0$ $I_{C}=-1mA, I_{B}=0$ $I_{E}=-10\mu A, I_{C}=0$ $V_{CB}=-200V, I_{E}=0$	-300 -300	-50	V V V nA	
BV _{CBO} BV _{CEO} BV _{EBO} ICBO	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage	$I_{C}=-100\mu A, I_{E}=0$ $I_{C}=-1mA, I_{B}=0$ $I_{E}=-10\mu A, I_{C}=0$ $V_{CB}=-200V, I_{E}=0$ $V_{EB}=-4V, I_{C}=0$	-300 -300		VV	
BV _{CBO} BV _{CEO} BV _{EBO}	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current	$\begin{split} & I_{C}\text{=}-100\mu\text{A}, I_{E}\text{=}0\\ & I_{C}\text{=}-1\text{mA}, I_{B}\text{=}0\\ & I_{E}\text{=}-10\mu\text{A}, I_{C}\text{=}0\\ & V_{CB}\text{=}-200\text{V}, I_{E}\text{=}0\\ & V_{EB}\text{=}-4\text{V}, I_{C}\text{=}0\\ & V_{CE}\text{=}-10\text{V}, I_{C}\text{=}-1\text{mA}\\ & V_{CE}\text{=}-10\text{V}, I_{C}\text{=}-10\text{mA} \end{split}$	-300 -300 -5	-50	V V V nA	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current	$\begin{array}{c c} I_{C}=-100\mu A, I_{E}=0\\ \hline I_{C}=-1mA, I_{B}=0\\ \hline I_{E}=-10\mu A, I_{C}=0\\ \hline V_{CB}=-200V, I_{E}=0\\ \hline V_{EB}=-4V, I_{C}=0\\ \hline V_{CE}=-10V, I_{C}=-1mA\\ \hline V_{CE}=-10V, I_{C}=-10mA\\ \hline V_{CE}=-10V, I_{C}=-30mA\\ \end{array}$	-300 -300 -5 -5 -5 	-50 -50 270	V V V nA	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current	$I_{C} = -100\mu A, I_{E} = 0$ $I_{C} = -1mA, I_{B} = 0$ $I_{E} = -10\mu A, I_{C} = 0$ $V_{CB} = -200V, I_{E} = 0$ $V_{EB} = -4V, I_{C} = 0$ $V_{CE} = -10V, I_{C} = -1mA$ $V_{CE} = -10V, I_{C} = -10mA$ $V_{CE} = -10V, I_{C} = -30mA$ $V_{CE} = -10V, I_{C} = -50mA$	-300 -300 -5 -5 -5 	-50	V V V nA	
3V _{CBO} 3V _{CEO} 3V _{EBO} CBO EBO PFE	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current	$\begin{array}{c c} I_{C}=-100\mu A, I_{E}=0\\ \hline I_{C}=-1mA, I_{B}=0\\ \hline I_{E}=-10\mu A, I_{C}=0\\ \hline V_{CB}=-200V, I_{E}=0\\ \hline V_{EB}=-4V, I_{C}=0\\ \hline V_{CE}=-10V, I_{C}=-1mA\\ \hline V_{CE}=-10V, I_{C}=-10mA\\ \hline V_{CE}=-10V, I_{C}=-30mA\\ \end{array}$	-300 -300 -5 -5 -5 	-50 -50 270	V V V nA	
3V _{CBO} 3V _{CEO} 3V _{EBO} CBO EBO PFE	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 -5 -5 	-50 -50 270 200 -0.30 -0.35	V V V nA nA V V V	
3V _{CBO} 3V _{CEO} 3V _{EBO} CBO EBO PFE	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 -5 -5 	-50 -50 270 200 -0.30 -0.35 -0.50	V V NA nA V V V V V	
3V _{CBO} 3V _{CEO} 3V _{EBO} cBO EBO PFE	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 -5 -5 	-50 -50 270 200 -0.30 -0.35 -0.50 -1	V V nA nA V V V V V V	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO hFE	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 -5 -5 	-50 -50 270 200 -0.30 -0.35 -0.50	V V NA nA V V V V V	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO hFE	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 -5 -5 	-50 -50 270 200 -0.30 -0.35 -0.50 -1 -0.75	V V V NA nA NA V V V V V V V V V	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO hFE V _{CE} (sat)	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 -5 -5 	-50 -50 270 200 -0.30 -0.35 -0.50 -1 -0.75 -0.85	V V NA NA NA V V V V V V V V V V	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO hFE V _{CE} (sat) V _{BE} (sat)	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 30 45 45 40 20	-50 -50 270 200 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90	V V NA NA NA V V V V V V V V V V V V V	
BV _{CBO} BV _{CEO} BV _{EBO} CBO EBO hFE V _{CE} (sat) V _{BE} (sat) V _{BE} (on) T C _{ob}	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage * Current Gain Bandwidth Product Output Capacitance	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 30 45 45 40 20	-50 -50 270 200 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90 -2 200 6	V V nA nA V PF	
$\frac{3V_{CBO}}{3V_{CBO}}$ $\frac{3V_{CBO}}{3V_{CBO}}$ $\frac{3V_{CBO}}{CBO}$ $\frac{CBO}{CBO}$ $\frac{CBO}{CBO}$ $\frac{CBO}{CE}$ $\frac{CE}{CE}$ $\frac{CE}{CEB}$	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain * DC Current Gain Base-Emitter Saturation Voltage * Current Gain Bandwidth Product Output Capacitance Emitter-Base Capacitance	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 30 45 45 40 20	-50 -50 270 200 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90 -2 200 6 100	V V nA nA V PF pF pF	
BV _{CBO} BV _{CEO} BV _{EBO} ICBO	Parameter Collector-Base Breakdown Voltage * Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage * Current Gain Bandwidth Product Output Capacitance	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-300 -300 -5 30 45 45 40 20	-50 -50 270 200 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90 -2 200 6	V V nA nA V PF	

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